NSN 5962-01-108-4756

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-108-4756

Body Length:

Between 0.750 inches and 0.795 inches

Body Width:

Between 0.245 inches and 0.300 inches

Body Height:

Between 0.120 inches and 0.195 inches

Maximum Power Dissipation Rating:

512.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and programmable and programmed and bipolar and 3-state output

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

Mo-001-ag joint electron device engineering council

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

35.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Rom

Test Data Document:

13499-351-7769 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

NSN 5962-01-108-4756

Memory Microcircuit - Page 2 of 2

Fiig: A458a0

